

Appl. No. 10/711,018
Amdt. dated January 28, 2005
Reply to Office action of 01/11/2005

Amendments to the Claims:

Listing of Claims:

Claim 1 (original) A storage capacitor having a scattering effect adapted
5 for use in a thin film transistor array loop, the storage capacitor
comprising:

- a first electrode positioned in a substrate, the first electrode
comprising a first conductive layer;
- 10 a rough layer positioned above the first electrode, the rough layer
comprising a medium layer and a passivation layer; and
- a second electrode, positioned above the rough layer, for
implementing the scattering effect toward an external light source.

Claim 2 (original) The storage capacitor of claim 1 wherein the
15 passivation layer is positioned above the medium layer.

Claim 3 (original) The storage capacitor of claim 1 wherein the medium
layer is positioned above the passivation layer.

20 Claim 4 (original) The storage capacitor of claim 1 wherein the second
electrode comprises a reflective layer with high reflectivity and
conductivity.

Claim 5 (original) The storage capacitor of claim 1 wherein the second
25 electrode comprises a second conductive layer and a reflective layer with
high reflectivity.

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Claim 6 (original) The storage capacitor of claim 5 wherein the reflective layer is positioned above the second conductive layer.

5 Claim 7 (original) The storage capacitor of claim 5 wherein the second conductive layer is light-penetrating and positioned above the reflective layer.

10 Claim 8 (original) The storage capacitor of claim 1 wherein the medium layer is composed of materials selected from a group consisting of indium oxide, tin oxide, zinc oxide, lead oxide, indium tin oxide, and indium zinc oxide.

15 Claim 9 (original) The storage capacitor of claim 1 wherein the passivation layer is composed of materials selected from a group consisting of silicon nitride, silicon oxide, and silicon oxynitride.

Claims 10-21 (cancelled)

20 Claim 22 (original) A storage capacitor having a scattering effect adapted for use in a thin film transistor array loop, the storage capacitor comprising:

25 a first electrode, positioned in a substrate, comprising a first conductive layer;
a dielectric layer positioned above the first electrode, the dielectric layer being insulating;
a second electrode, positioned above the dielectric layer, comprising a second conductive layer, a rough layer, and a reflective layer with high reflectivity, the rough layer being positioned above the second

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conductive layer and comprising a medium layer and a passivation layer, the passivation layer being positioned above the medium layer, the reflective layer being positioned above the rough layer.

5 Claim 23 (original) The storage capacitor of claim 22 wherein the medium layer is composed of materials selected from a group consisting of indium oxide, tin oxide, zinc oxide, lead oxide, indium tin oxide, and indium zinc oxide.

10 Claim 24 (original) The storage capacitor of claim 22 wherein the passivation layer is composed of materials selected from a group consisting of silicon nitride, silicon oxide, and silicon oxynitride.

15 Claim 25 (original) A storage capacitor having a scattering effect adapted for use in a thin film transistor array loop, the storage capacitor comprising:

20 a first electrode, positioned in a substrate, comprising a rough layer and a first conductive layer, the rough layer comprising a medium layer and a passivation layer, the medium layer being positioned above the passivation layer, the first conductive layer being positioned above the rough layer;
a dielectric layer positioned above the first electrode, the dielectric layer being insulating; and
25 a second electrode positioned above the dielectric layer for implementing the scattering effect toward an external light source.

Claim 26 (original) The storage capacitor of claim 25 wherein the medium layer is composed of materials selected from a group consisting of indium

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oxide, tin oxide, zinc oxide, lead oxide, indium tin oxide, and indium zinc oxide.

5 Claim 27 (original) The storage capacitor of claim 25 wherein the passivation layer is composed of materials selected from a group consisting of silicon nitride, silicon oxide, and silicon oxynitride.

Claim 28 (original) The storage capacitor of claim 25 wherein the second electrode comprises a reflective layer with high reflectivity.

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Claim 29 (original) The storage capacitor of claim 25 wherein the second electrode comprises a second conductive layer and a reflective layer with high reflectivity, the reflective layer being positioned above the second conductive layer.

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